



A Product Line of Diodes Incorporated



ZXTN25040DFH

40V NPN MEDIUM POWER PLANAR TRANSISTOR IN SOT23

Features and Benefits

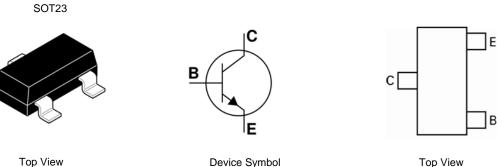
- BV_{CEO} > 40V
- I_C = 4A Continuous Collector Current
- Low Saturation Voltage V_{CE(sat)} < 55mV @ 1A
- R_{CE(sat)} = 35mΩ
- h_{FE} characterised up to 10A
- High h_{FE} min 300 @ 1A
- 1.25W power dissipation
- 130V forward blocking voltage
- 6V reverse blocking voltage
- Complementary part number ZXTP25040DFH
- "Lead-Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free. "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- Case material: Molded Plastic. "Green" Molding Compound (Note 2) UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish; Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (Approximate)

Applications

- MOSFET gate drivers
- Power switches
- Motor control
- DC fans
- DC-DC converters



Top View Pin Configuration

Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel	
ZXTN25040DFHTA	1A4	7	8	3,000	

Notes: 1. No purposefully added lead.

2. Diodes Inc's "Green" Policy can be found on our website at https://www.diodes.com/

3. Devices with lot number starting from PID0155145 (March 2010) are "Green" products.

Marking Information





Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	;	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	130	V	
Collector-Emitter Voltage (Forward Block	ng)	V _{CEX}	130	V
Collector-Emitter Voltage		V _{CEO}	40	V
Emitter-Collector Voltage (Reverse Blocking)		V _{ECO}	6	V
Emitter-Base Voltage		V _{EBO}	7	V
Continuous Collector Current	(Note 6)	lc	4	A
Peak Pulse Current		ICM	10	A
Base Current		IB	1	А

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit	
	(Note 4)		0.73 5.84	
Power Dissipation	(Note 5)	PD	1.05 8.4	W
Linear Derating Factor	(Note 6)		1.25 9.6	mW/°C
	(Note 7)		1.81 14.5	
	(Note 4)		171	
Thermal Desistance, lunction to Archient	(Note 5)		119	00111
Thermal Resistance, Junction to Ambient	(Note 6)	R _{θJA}	100	°C/W
	(Note 7)		69	
Thermal Resistance, Junction to Lead (Note 8)		R _{θJL}	74.95	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

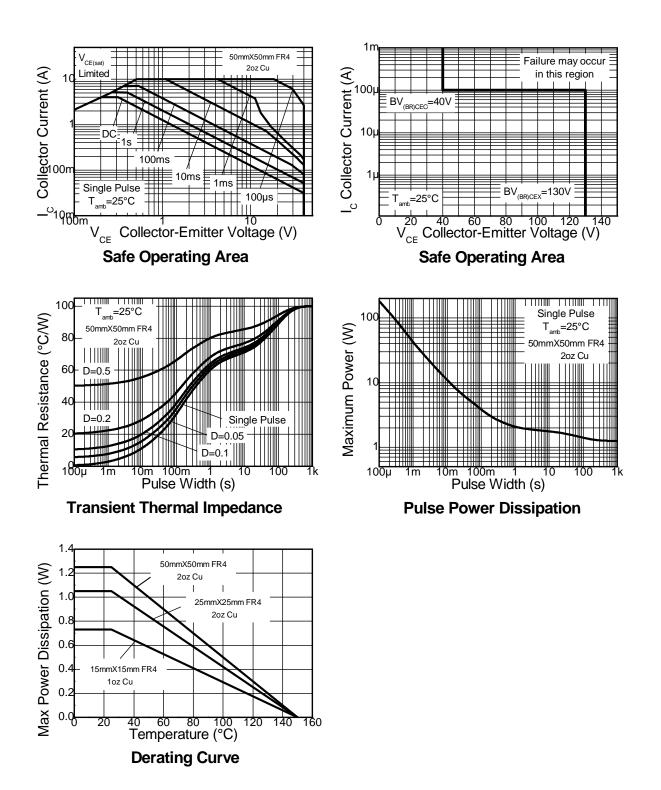
Notes: 4. For a device surface mounted on 15mm X 15mm X 1.6mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

5. For a device surface mounted on 25mm X 25mm X 1.6mm FR4 PCB with high coverage of single sided 2 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

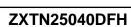
6. For a device surface mounted on 50mm X 50mm X 1.6mm FR4 PCB with high coverage of single sided 2 oz copper, in still air conditions; the device is no a device sufface sufface induities in a steady-state condition.
7. As note 6 above, measured at t < 5 seconds
8. Thermal resistance from junction to solder-point (at the end of the collector lead).



Typical Thermal Characteristics





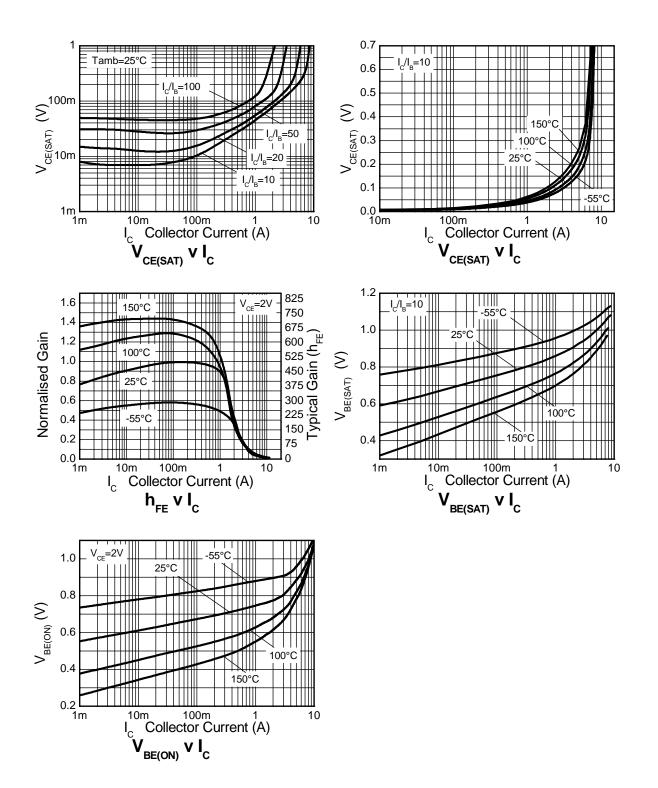


Electrical Characteristics @T _A = 25°C unless otherwise specified								
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS								
Collector-Base Breakdown Voltage	BV _{CBO}	130	170	-	V	I _C = 100μA		
Collector-emitter breakdown voltage (forward blocking)	BV _{CEX}	130	170	-	V	$I_C = 100\mu$ A; $R_{BE} < 1k\Omega$ or -1V < V _{BE} < 0.25V		
Collector-Emitter Breakdown Voltage (base open) (Note 9)	BV _{CEO}	40	63	-	V	I _C = 10mA		
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.3	-	V	I _E = 100μA		
Emitter-collector breakdown voltage (reverse blocking)	BV _{ECX}	6	7.4	-	V	$I_E = 100 \mu A$; R _{BC} < 1kΩ or -0.25V < V _{BC} < 0.25V		
Emitter-collector breakdown voltage (base open)	BV _{ECO}	6	7.4	-	V	I _E = 100μA;		
Collector-base Cut-off Current	I _{CBO}	-	<1 -	50 20	nΑ μΑ	V _{CB} = 100V V _{CB} = 100V, T _A = 100°C		
Collector-emitter Cut-off Current	I _{CEX}	-	-	100	nA	V_{CE} = 100V; R_{BE} < 1k Ω or -1V < V_{BE} < 0.25V		
Emitter-base Cut-off Current	I _{EBO}	-	<1	50	nA	V _{EB} = 5.6V		
ON CHARACTERISTICS (Note 9)								
Static Forward Current Transfer Ratio	h _{FE}	300 300 30 -	450 450 60 10	900 - - -	-	$I_{C} = 10mA, V_{CE} = 2V$ $I_{C} = 1A, V_{CE} = 2V$ $I_{C} = 4A, V_{CE} = 2V$ $I_{C} = 10A, V_{CE} = 2V$		
Collector-Emitter Saturation Voltage	V _{CE(sat)}	-	45 120 135 140	55 210 210 190	mV	$\begin{split} &I_{C} = 1A, I_{B} = 100 \text{mA} \\ &I_{C} = 1A, I_{B} = 10 \text{mA} \\ &I_{C} = 2A, I_{B} = 40 \text{mA} \\ &I_{C} = 4A, I_{B} = 400 \text{mA} \end{split}$		
Base-Emitter Saturation Voltage	V _{BE(sat)}	-	960	1050	mV	$I_{C} = 4A, I_{B} = 400mA$		
Base-Emitter On Voltage	V _{BE(on)}	-	840	950	mV	$I_C = 4A, V_{CE} = 2V$		
SMALL SIGNAL CHARACTERISTICS (Note 9)								
Transition Frequency	f⊤	-	190	-	MHz	$I_{C} = 50 \text{mA}, V_{CE} = 10 \text{V},$ f = 100MHz		
Collector Output Capacitance	Cobo	-	11.7	20	pF	$V_{CB} = 10V$, f = 1MHz		
Delay time	t _d	-	64	-	ns	101/		
Rise time	t _r	-	108	-	ns	$V_{\rm CC} = 10V,$		
Storage time	ts	-	428	-	ns	$I_{C} = 1A,$ $I_{B1} = I_{B2} = 10mA$		
Fall time	t _f	-	130	-	ns	$_{\rm B1}{\rm B2} = 1000$		

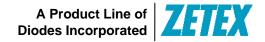
Notes: 9. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%



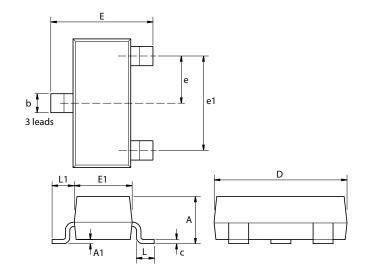
Typical Electrical Characteristics







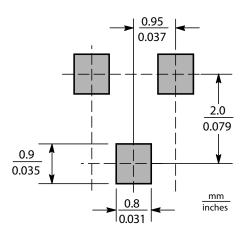
Package Outline Dimensions



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
А	-	1.12	-	0.044	e1	1.90 NOM		0.075 NOM	
A1	0.01	0.10	0.0004	0.004	E	2.10	2.64	0.083	0.104
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055
с	0.085	0.20	0.003	0.008	L	0.25	0.60	0.0098	0.0236
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024
е	0.95	NOM	0.037	NOM	-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

Suggested Pad Layout





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